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November 2013

FGH30T65UPDT 650V, 30A Field Stop Trench IGBT

Features

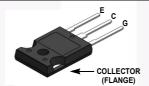
- Maximum Junction Temperature : T_J = 175°C
- Positive Temperaure Co-efficient for Easy Parallel Operating
- **High Current Capability**
- Low Saturation Voltage: $V_{CE(sat)} = 1.65 \text{ V (Typ.)} @ I_C = 30 \text{ A}$
- 100% of Parts Tested I_{LM(2)}
- High Input Impedance
- **Tightened Parameter Distribution**
- **RoHS Compliant**
- Short Circuit Ruggedness > 5 us @ 25°C

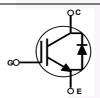
General Description

Using novel field stop trench IGBT technology, Fairchild's new series of field stop trench IGBTs offer the optimum performance for solar inverter, UPS and digital power generator where low conduction and switching losses are essential.

Applications

· Solar Inverter, UPS, Digital Power Generator





Absolute Maximum Ratings

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		650	V	
V _{GES}	Gate to Emitter Voltage		± 20	V	
V GES	Transient Gate to Emitter Voltage		± 25	V	
I _C	Collector Current	@ T _C = 25°C	60	А	
'C	Collector Current	@ T _C = 100°C	30	Α	
I _{CM(1)}	Pulsed Collector Current		90	А	
I _{LM(2)}	Clamped Inductive Load Current		90	А	
l _F	Diode Forward Current	@ T _C = 25°C	60	A	
	Diode Forward Current	@ T _C = 100°C	30	Α	
I _{FM(1)}	Pulsed Diode Maximum Forward Current		150	A	
P _D	Maximum Power Dissipation	@ T _C = 25°C	250	W	
	Maximum Power Dissipation	@ T _C = 100°C	125	W	
SCWT	Short Circuit Withstand Time @ T _C = 25°C		5	us	
T _J	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°С	

Notes:
1: Repetitive rating: Pulse width limited by max. junction temperature

2: I_C = 90 A, V_{CC} = 400 V, R_g = 20 Ω

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JC}(IGBT)$	R _{0JC} (IGBT) Thermal Resistance, Junction to Case		0.60	°C/W
R _{θJC} (Diode) Thermal Resistance, Junction to Case		-	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	-	40	°C/W

Package Marking and Ordering Information

Part Number	art Number Top Mark		Packing Method	Reel Size	Tape Width	Quantity
FGH30T65UPD_F155	FGH30T65UPD	TO-247 G03	Tube	N/A	N/A	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	teristics					
BV _{CES}	Collector to Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 1 mA	650	-	-	V
$\frac{\Delta BV_{CES}}{\Delta T_{J}}$	Temperature Coefficient of Breakdown Voltage	V _{GE} = 0 V, I _C = 250 uA	-	0.65	-	V/°C
I _{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$	/-	-	250	μΑ
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$	-	-	±400	nA
On Charac	teristics					
V _{GE(th)}	G-E Threshold Voltage	I_C = 30 mA, V_{CE} = V_{GE}	4.0	6.0	7.5	V
()		I _C = 30 A, V _{GE} = 15 V	-	1.65	2.3	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 30 A, V _{GE} = 15 V, T _C = 175°C	-	2.1	-	V
Dynamic C	haracteristics					
C _{ies}	Input Capacitance		-	2280	-	pF
C _{oes}	Output Capacitance	$V_{CE} = 30 \text{ V}, V_{GE} = 0 \text{ V},$	_	85	-	pF
C _{res}	Reverse Transfer Capacitance	f = 1 MHz	-	40	-	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{CC} = 400 V, I _C = 30 A,	-	22	-	ns
t _r	Rise Time		-	26	-	ns
t _{d(off)}	Turn-Off Delay Time		-	139	-	ns
t _f	Fall Time	$R_G = 8 \Omega, V_{GE} = 15 V,$	-	18	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 25°C	-/	0.76	-	mJ
E _{off}	Turn-Off Switching Loss		-	0.40	-	mJ
E _{ts}	Total Switching Loss		-	1.16	- /	mJ
t _{d(on)}	Turn-On Delay Time		-	22	-	ns
t _r	Rise Time		-	30	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 400 \text{ V, } I_{C} = 30 \text{ A,}$	-	151	- /	ns
t _f	Fall Time	$R_G = 8 \Omega$, $V_{GE} = 15V$,	-	19	-	ns
E _{on}	Turn-On Switching Loss	Inductive Load, T _C = 175°C	-	1.20	- \	mJ
E _{off}	Turn-Off Switching Loss		-	0.53	-	mJ
E _{ts}	Total Switching Loss		-	1.73	-	mJ
Tsc	Short Circuit Withstand Time	$V_{\rm GE}$ = 15 V, $V_{\rm CC}$ \leq 400 V, Rg = 10 Ω	5	-	-	us
Q _g	Total Gate Charge		-	155	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 400 \text{ V}, I_{C} = 30 \text{ A},$	-	21	-	nC
Q _{gc}	Gate to Collector Charge	V _{GE} = 15 V	-	91	-	nC

Electrical Characteristics of the Diode $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Тур.	Max	Unit
V _{FM}	Diode Forward Voltage	I _E = 30 A	$T_C = 25^{\circ}C$	-	2.3	3.0	V
FIVI	2.000 r o.ma.u romago	1F 0071	$T_{\rm C} = 175^{\rm o}{\rm C}$	-	1.9	-	
E _{rec}	Reverse Recovery Energy		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	35	-	uJ
t _{rr}	Diode Reverse Recovery Time	I _F = 30 A, di _F /dt = 200 A/μs	$T_C = 25^{\circ}C$	-	33	43	ns
भा	Blodd Neveron Necestery Time	ης σο τι, αιρταί 200 τυμο	T _C = 175°C	-	148		110
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	-	57	80	nC
~ii	2.000 No.000 No.00101 y Change		$T_{\rm C} = 175^{\rm o}{\rm C}$	-	560		::0

Figure 1. Typical Output Characteristics

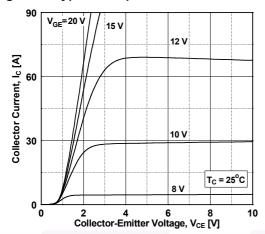


Figure 3. Typical Saturation Voltage Characteristics

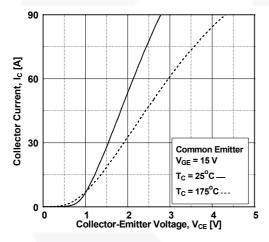


Figure 5. Saturation Voltage vs. V_{GE}

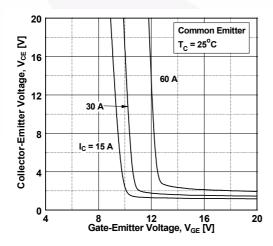


Figure 2. Typical Output Characteristics

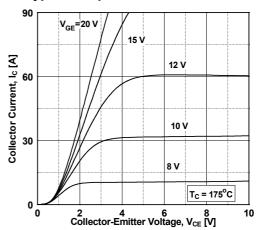


Figure 4. Saturation Voltage vs. Case
Temperature at Variant Current Leve

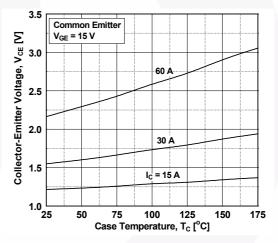


Figure 6. Saturation Voltage vs. V_{GE}

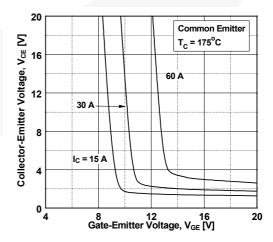


Figure 7. Capacitance Characteristic

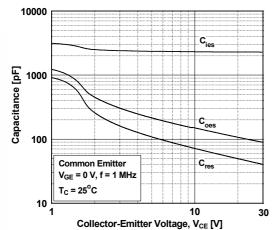


Figure 9. Turn-on Characteristics vs.
Gate Resistance

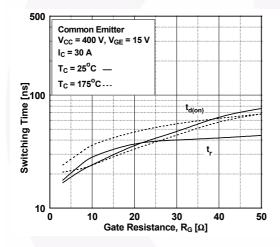


Figure 11. Switching Loss vs. Gate Resistance

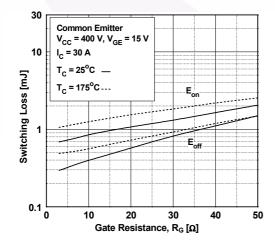


Figure 8. Gate charge Characteristics

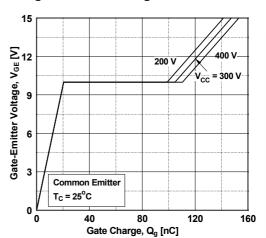


Figure 10. Turn-off Characteristics vs. Gate Resistance

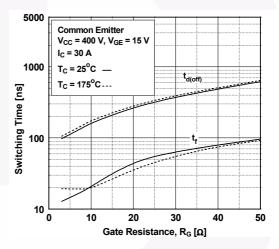


Figure 12. Turn-on Characteristics vs.
Collector Current

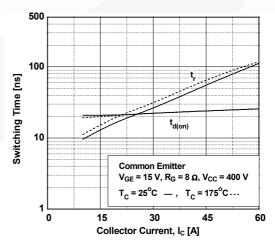


Figure 13. Turn-off Characteristics vs. Collector Current

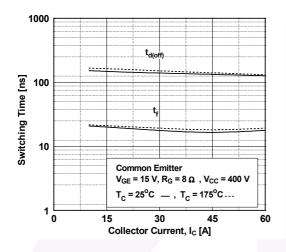


Figure 15. Load Current vs. Frequency

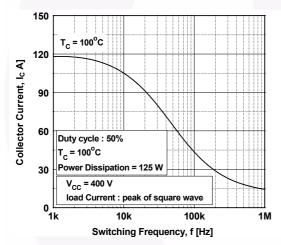


Figure 17. Forward Characteristics

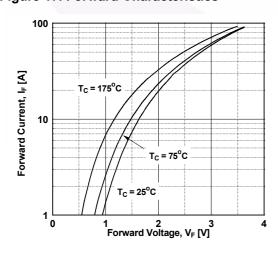


Figure 14. Switching Loss vs. Collector Current

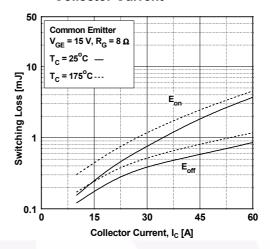


Figure 16. SOA Characteristics

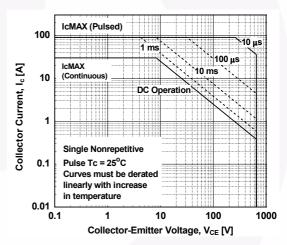


Figure 18. Reverse Revovery Current

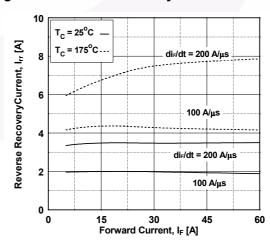


Figure 19. Reverse Recovery Time

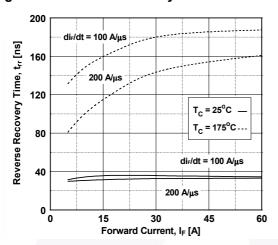


Figure 20. Stored Charge

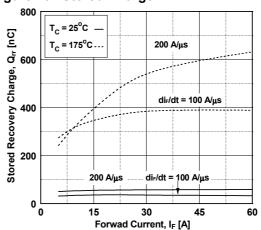


Figure 21. Transient Thermal Impedance of IGBT

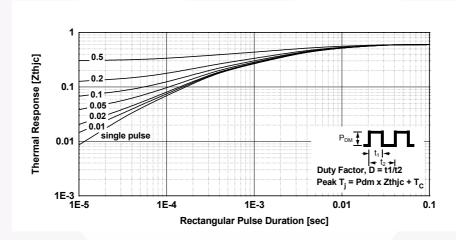
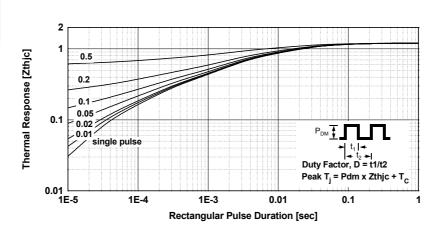
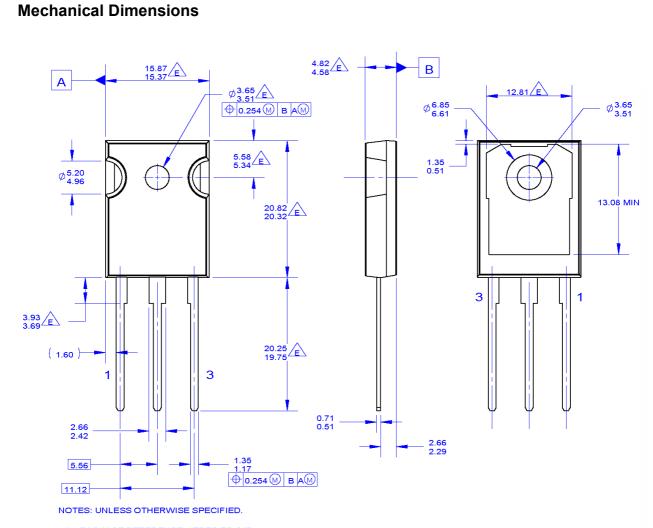


Figure 22. Transient Thermal Impedance of Diode





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- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD
- FLASH, AND TIE BAR EXTRUSIONS.
 C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 1994
- DOES NOT COMPLY JEDEC STANDARD VALUE
- F. DRAWING FILENAME: MKT-TO247G03_REV01

Figure 23. TO247, Molded, 3-Lead, JEDEC AB Long Lead

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Dimensions in Millimeters





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